



Precision Monolithic Low-Voltage CMOS Analog Switches

FEATURES

- 2.7- thru 12-V Single Supply or ± 3 - thru ± 6 -Dual Supply
- On-Resistance— r_{ON} : 14 Ω
- Fast Switching— t_{ON} : 28 ns
— t_{OFF} : 13 ns
- TTL, CMOS Compatible
- Low Leakage: < 100 pA

BENEFITS

- Widest Dynamic Range
- Low Signal Errors and Distortion
- Break-Before-Make Switching Action
- Simple Interfacing

APPLICATIONS

- Precision Automatic Test Equipment
- Precision Data Acquisition
- Communication Systems
- Battery Powered Systems
- Computer Peripherals
- SDSL, DSLAM
- Audio and Video Signal Routing

DESCRIPTION

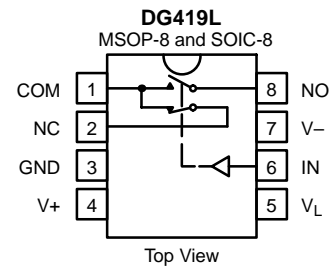
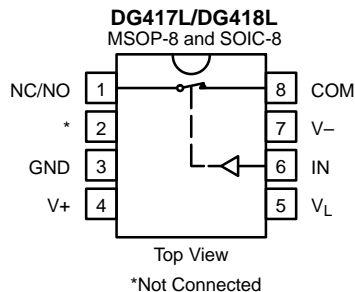
The DG417L/418L/419L are low voltage pin-for-pin compatible companion devices to the industry standard DG417/418/419 with improved performance

Using BiCMOS wafer fabrication technology allows the DG417L/418L/419L to operate on single and dual supplies. Single supply voltage ranges from 3 to 12 V while dual supply operation is recommended with ± 3 to ± 6 V.

Combining high speed (t_{ON} : 28 ns), flat r_{ON} over the analog signal range (6 Ω), minimal insertion lose (up to 100 MHz), and excellent crosstalk and off-isolation performance (-70 dB at 1 MHz), the DG417L/418L/419L are ideally suited for audio and video signal switching.

The DG417L and DG418L respond to opposite control logic as shown in the Truth Table. The DG419L has an SPDT configuration.

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE		
Logic	DG417L	DG418L
0	ON	OFF
1	OFF	ON

TRUTH TABLE—DG419L		
Logic	SW ₁	SW ₂
0	ON	OFF
1	OFF	ON

ORDERING INFORMATION-DG417L/418L		
Temp Range	Package	Part Number
-40 to 85°C	8-Pin Narrow SOIC	DG417LDY
		DG418LDY
	8-Pin MSOP	DG417LDQ
		DG418LDQ

ORDERING INFORMATION-DG419L		
Temp Range	Package	Part Number
-40 to 85°C	8-Pin Narrow SOIC	DG419LDY
	8-Pin MSOP	DG419LDQ



ABSOLUTE MAXIMUM RATINGS

V+ to V-	-0.3 TO 13 V
GND to V-	7 V
V _L	(GND -0.3 V) to (V+) +0.3 V
I _N , COM, NC, NO ^a	-0.3 to (V+ +0.3 V) or 30 mA, whichever occurs first
Continuous Current (Any Terminal)	30 mA
Peak Current, S or D (Pulsed 1 ms, 10% Duty Cycle)	100 mA
Storage Temperature (DQ, DY Suffix)	-65 to 150°C

Power Dissipation (Package)^b

8-Pin MSOP ^c	320 mW
8-Pin SOIC ^c	400 mW

Notes:

- Signals on NC, NO, COM, or IN exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- All leads welded or soldered to PC Board.
- Derate 6.5 mW/°C above 25°C

SPECIFICATIONS (SINGLE SUPPLY 12 V)							
Parameter	Symbol	Test Conditions Unless Specified V+ = 12 V, V- = 0 V V _L = 5 V, V _{IN} = 2.4 V, 0.8 V ^f	Temp ^b	Limits -40 to 85°C			Unit
				Min ^d	Typ ^c	Max ^d	
Analog Switch							
Analog Signal Range ^e	V _{ANALOG}		Full	0		12	V
On-Resistance	r _{ON}	V+ = 10.8 V, V- = 0 V I _{NO} , I _{NC} = 5 mA, V _{COM} = 2/9 V	Room Full		13	20 23.5	Ω
Switch Off Leakage Current	I _{NO(off)} , I _{NC(off)}	V _{COM} = 1/11 V V _{NO} , V _{NC} = 11/1 V	Room Full	-0.15 -2.5		0.15 2.5	nA
	I _{COM(off)}		Room Full	-0.15 -2.5		0.15 2.5	
Channel On Leakage Current	I _{COM(on)}	V _{NO} , V _{NC} = V _{COM} = 11/1 V	Room Full	-0.2 -3		0.2 3	
Digital Control							
Input Current	I _{INL} or I _{INH}		Full	-1	0.01	1	μA
Dynamic Characteristics							
Turn-On Time	t _{ON}	R _L = 300 Ω, C _L = 35 pF V _{NO} , V _{NC} = 5 V See Figure 2	Room Full		28	43 46	ns
Turn-Off Time	t _{OFF}		Room Full		13	31 32	
Break-Before-Make Time Delay	t _D	DG419L Only, V _{NC} , V _{NO} = 5 V R _L = 300 Ω, C _L = 35 pF	Room		13		
Charge Injection ^e	Q _{INJ}	V _g = 0 V, R _g = 0 Ω, C _L = 1 nF	Room		1		pC
Off Isolation ^e	OIRR	R _L = 50 Ω, C _L = 5 pF f = 1 MHz	Room		-71		dB
Channel-to-Channel Crosstalk ^e	X _{TALK}		Room		-71		
Source Off Capacitance ^e	C _{NO(off)} , C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		5		pF
Channel On Capacitance ^e	C _{ON}		Room		15		
Power Supplies							
Positive Supply Current	I+	V _{IN} = 0 or V _L	Room Full		0.02	1 5	μA
Negative Supply Current	I-		Room Full	-1 -5	-0.002		
Logic Supply Current	I _L		Room Full		0.002	1 5	
Ground Current	I _{GND}		Room Full	-1 -5	-0.002		



SPECIFICATIONS (DUAL SUPPLY ± 5 V)

Parameter	Symbol	Test Conditions Unless Specified $V_+ = 5\text{ V}, V_- = -5\text{ V}$ $V_L = 5\text{ V}, V_{IN} = 2.4\text{ V}, 0.8\text{ V}^f$	Temp ^b	Limits -40 to 85°C			Unit
				Min ^d	Typ ^c	Max ^d	
Analog Switch							
Analog Signal Range ^e	V_{ANALOG}		Full	-5		5	V
On-Resistance	r_{ON}	$V_+ = 5\text{ V}, V_- = -5\text{ V}$ $I_{NO}, I_{NC} = 5\text{ mA}, V_{COM} = \pm 3.5\text{ V}$	Room Full		14	18.5 21	Ω
Switch Off Leakage Current ^a	$I_{NO(off)}, I_{NC(off)}$	$V_+ = 5\text{ V}, V_- = -5\text{ V}$ $V_{COM} = \pm 4.5\text{ V}, V_{NO}, V_{NC} = \mp 4.5\text{ V}$	Room Full	-0.15 -2.5		0.15 2.5	nA
	$I_{COM(off)}$		Room Full	-0.15 -2.5		0.15 2.5	
Channel On Leakage Current ^a	$I_{COM(on)}$	$V_+ = 5\text{ V}, V_- = -5\text{ V}$ $V_{NO}, V_{NC} = V_{COM} = \pm 4.5\text{ V}$	Room Full	-0.2 -3		0.2 3	
Digital Control							
Input Current ^a	I_{INL} or I_{INH}		Full	-1	0.05	1	μA
Dynamic Characteristics							
Turn-On Time	t_{ON}	$R_L = 300\ \Omega, C_L = 35\text{ pF}$ $V_{NO}, V_{NC} = \pm 3.5\text{ V}$ See Figure 2	Room Full		30	41 44	ns
Turn-Off Time	t_{OFF}		Room Full		16	32 33	
Break-Before-Make Time Delay ^e	t_D	DG419L Only, $V_{NO}, V_{NC} = 3.5\text{ V}$ $R_L = 300\ \Omega, C_L = 35\text{ pF}$	Room		10		
Transition Time	t_{TRANS}	$R_L = 300\ \Omega, C_L = 35\text{ pF}$ $V_{S1} = \pm 3.5\text{ V}, V_{S2} = \mp 3.5\text{ V}$	Room		33	47	
Charge Injection ^e	Q_{INJ}	$V_g = 0\text{ V}, R_g = 0\ \Omega, C_L = 1\text{ nF}$	Room		3		pC
Off Isolation ^e	OIRR	$R_L = 50\ \Omega, C_L = 5\text{ pF}$ $f = 1\text{ MHz}$	Room		-71		dB
Channel-to-Channel Crosstalk ^e	X_{TALK}		Room		-76		
Source Off Capacitance ^e	$C_{NO(off)}, C_{NC(off)}$	$f = 1\text{ MHz}$	Room		5.2		pF
Channel On Capacitance ^e	C_{ON}		Room		15		
Power Supplies							
Positive Supply Current ^e	I_+	$V_{IN} = 0\text{ or }V_L$	Room Full		0.03	1 5	μA
Negative Supply Current ^e	I_-		Room Full	-1 -5	-0.002		
Logic Supply Current ^e	I_L		Room Full		0.002	1 5	
Ground Current ^e	I_{GND}		Room Full	-1 -5	-0.002		

SPECIFICATIONS (SINGLE SUPPLY 5 V)

Parameter	Symbol	Test Conditions Unless Specified $V_+ = 5\text{ V}, V_- = 0\text{ V}$ $V_L = 5\text{ V}, V_{IN} = 2.4\text{ V}, 0.8\text{ V}^f$	Temp ^b	Limits -40 to 85°C			Unit
				Min ^d	Typ ^c	Max ^d	
Analog Switch							
Analog Signal Range ^e	V_{ANALOG}		Full			5	V
On-Resistance ^e	r_{ON}	$V_+ = 4.5\text{ V}, I_{NO}, I_{NC} = 5\text{ mA}$ $V_{COM} = 1\text{ V}, 3.5\text{ V}$	Room Full		26	36.5 40.5	Ω
Dynamic Characteristics							
Turn-On Time ^e	t_{ON}	$R_L = 300\ \Omega, C_L = 35\text{ pF}$ $V_{NO}, V_{NC} = 3.5\text{ V}$, See Figure 2	Room Full		37	49 54	ns
Turn-Off Time ^e	t_{OFF}		Room Full		16	31 32	
Break-Before-Make Time Delay ^e	t_D	DG419L Only, $V_{NO}, V_{NC} = 3.5\text{ V}$ $R_L = 300\ \Omega, C_L = 35\text{ pF}$	Room		19		
Charge Injection ^e	Q_{INJ}	$V_g = 0\text{ V}, R_g = 0\ \Omega, C_L = 1\text{ nF}$	Room		0.4		pC



SPECIFICATIONS (SINGLE SUPPLY 5 V)							
Parameter	Symbol	Test Conditions Unless Specified $V_+ = 5\text{ V}, V_- = 0\text{ V}$ $V_L = 5\text{ V}, V_{IN} = 2.4\text{ V}, 0.8\text{ V}^f$	Temp ^b	Limits -40 to 85°C			Unit
				Min ^d	Typ ^c	Max ^d	
Power Supplies							
Positive Supply Current ^e	I+	$V_{IN} = 0\text{ or }V_L$	Room Full		0.02	1 5	μA
Negative Supply Current ^e	I-		Room Full	-1 -5	-0.002		
Logic Supply Current ^e	I _L		Room Full		0.002	1 5	
Ground Current ^e	I _{GND}		Room Full	-1 -5	-0.002		

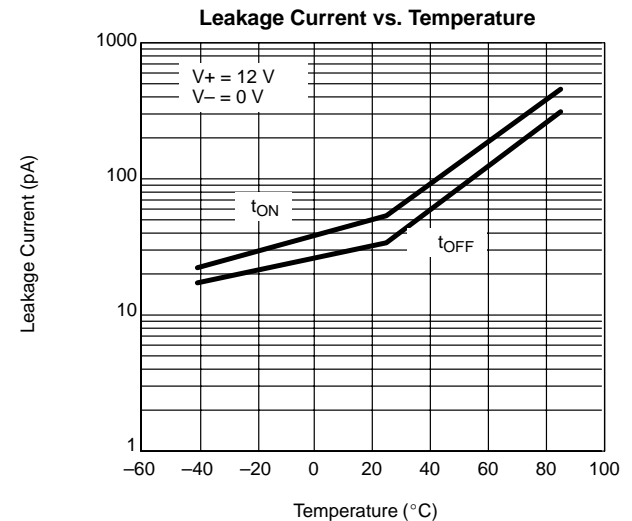
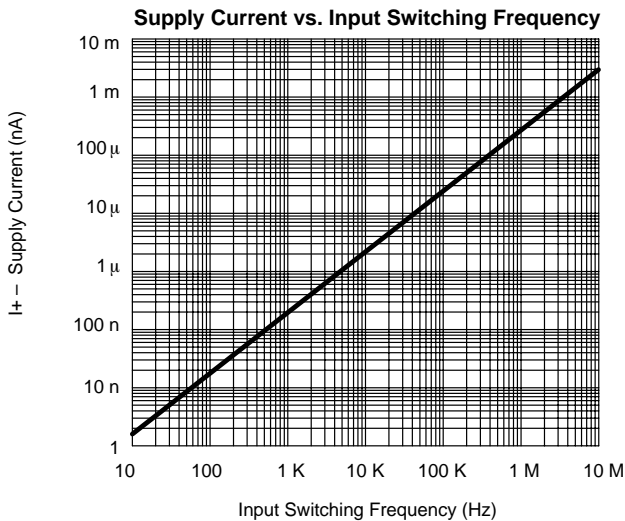
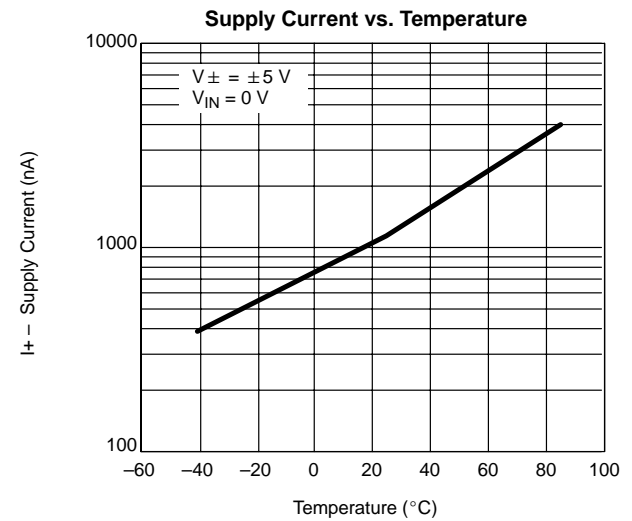
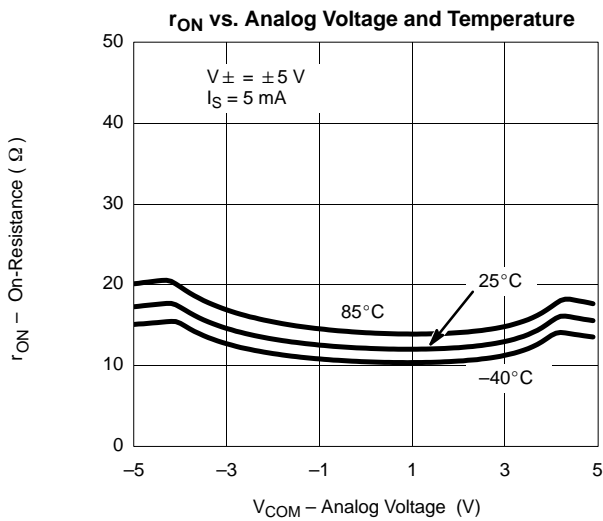
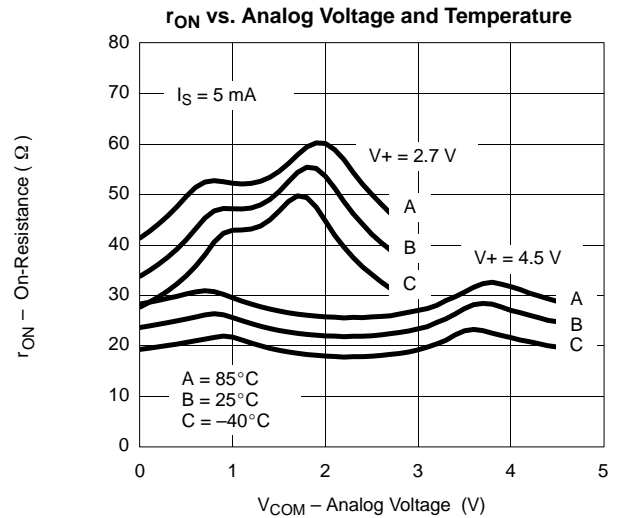
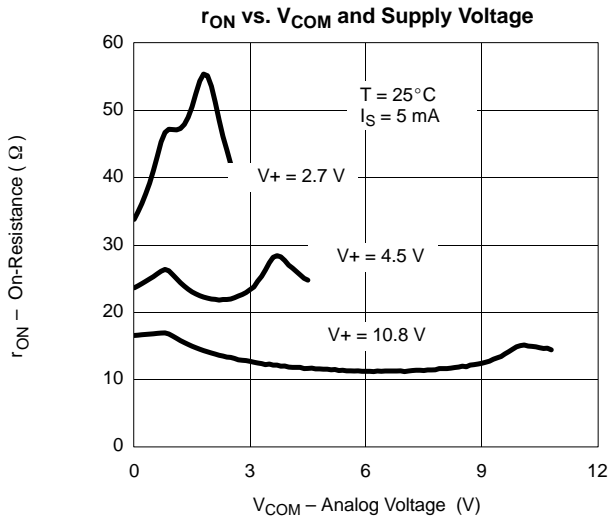
SPECIFICATIONS (SINGLE SUPPLY 3 V)							
Parameter	Symbol	Test Conditions Unless Specified $V_+ = 3\text{ V}, V_- = 0\text{ V}$ $V_L = 3\text{ V}, V_{IN} = 2.0\text{ V}, 0.4\text{ V}^f$	Temp ^b	Limits -40 to 85°C			Unit
				Min ^d	Typ ^c	Max ^d	
Analog Switch							
Analog Signal Range ^e	V _{ANALOG}		Full	0		3	V
On-Resistance	r _{ON}	$V_+ = 2.7\text{ V}, V_- = 0\text{ V}$ $I_{NO}, I_{NC} = 5\text{ mA}, V_{COM} = 0.5, 2.2\text{ V}$	Room Full		47	70 75	Ω
Switch Off Leakage Current ^a	I _{NO(off)} , I _{NC(off)}	$V_+ = 3\text{ V}, V_- = 0\text{ V}$ $V_{COM} = 1, 2\text{ V}, V_{NO}, V_{NC} = 2, 1\text{ V}$	Room Full	-0.15 -2.5		0.15 2.5	nA
	I _{COM(off)}		Room Full	-0.15 -2.5		0.15 2.5	
Channel On Leakage Current ^a	I _{COM(on)}	$V_+ = 3\text{ V}, V_- = 0\text{ V}$ $V_{NO}, V_{NC} = V_{COM} = 1, 2\text{ V}$	Room Full	-0.2 -3		0.2 3	
Digital Control							
Input Current ^a	I _{INL} or I _{INH}		Full	-1	0.005	1	μA
Dynamic Characteristics							
Turn-On Time	t _{ON}	$R_L = 300\text{ Ω}, C_L = 35\text{ pF}$ $V_{NO}, V_{NC} = 1.5\text{ V}$ See Figure 2	Room Full		65	75 85	ns
Turn-Off Time	t _{OFF}		Room Full		26	41 43	
Break-Before-Make Time Delay	t _D	DG419L Only, $V_{NO}, V_{NC} = 1.5\text{ V}$ $R_L = 300\text{ Ω}, C_L = 35\text{ pF}$	Room		33		
Charge Injection ^e	Q _{INJ}	$V_g = 0\text{ V}, R_g = 0\text{ Ω}, C_L = 1\text{ nF}$	Room		1		pC
Off Isolation ^e	OIRR	$R_L = 50\text{ Ω}, C_L = 5\text{ pF}$ $f = 1\text{ MHz}$	Room		-71		dB
Channel-to-Channel Crosstalk ^e	X _{TALK}		Room		-77		
Source Off Capacitance ^e	C _{NO(off)} , C _{NC(off)}	$f = 1\text{ MHz}$	Room		5.6		pF
Channel On Capacitance ^e	C _{D(on)}		Room		16		

Notes:

- Leakage parameters are guaranteed by worst case test condition and not subject to production test.
- Room = 25°C, Full = as determined by the operating temperature suffix.
- Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- Guaranteed by design, not subject to production test.
- V_{IN} = input voltage to perform proper function.

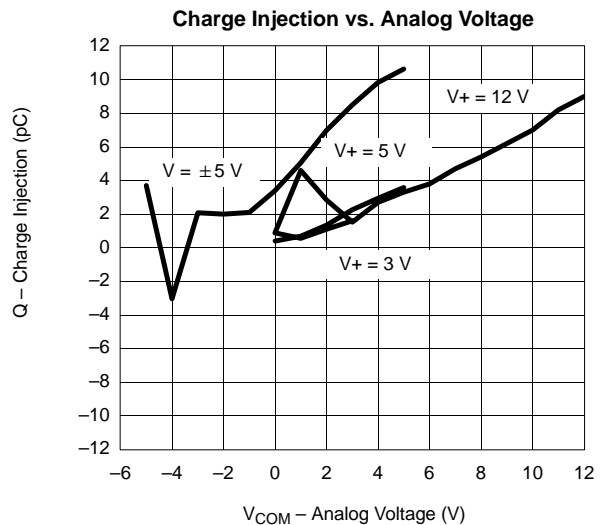
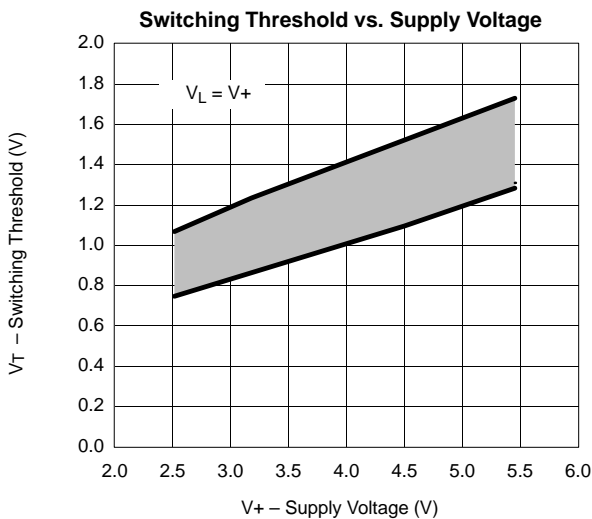
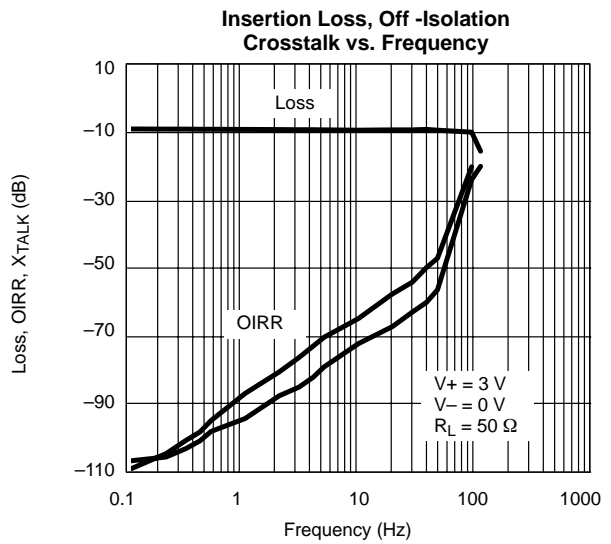
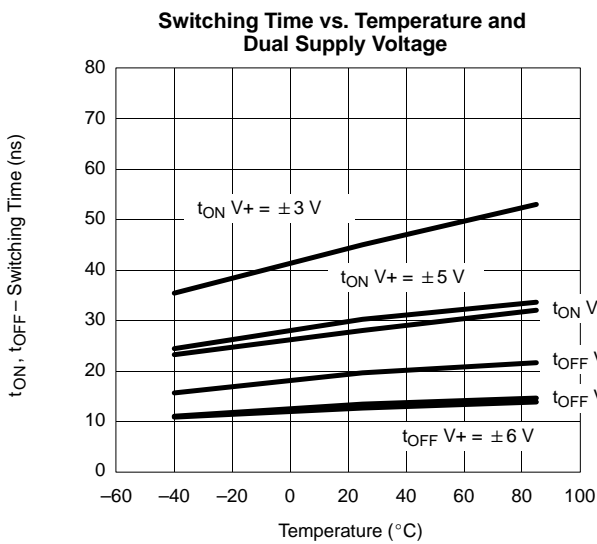
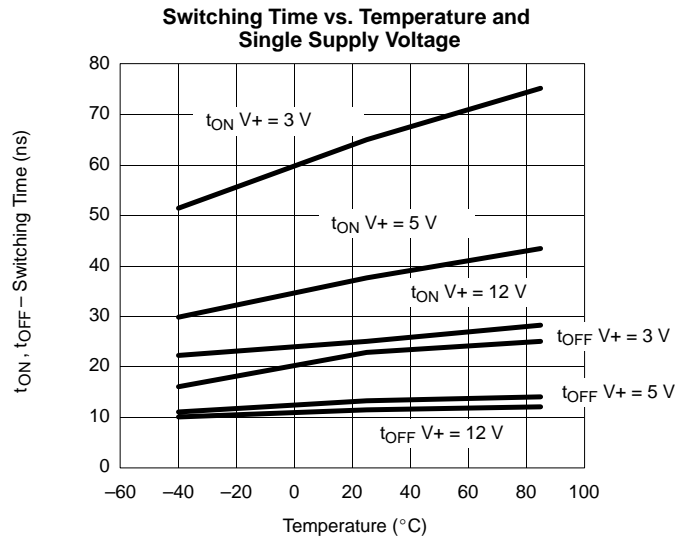
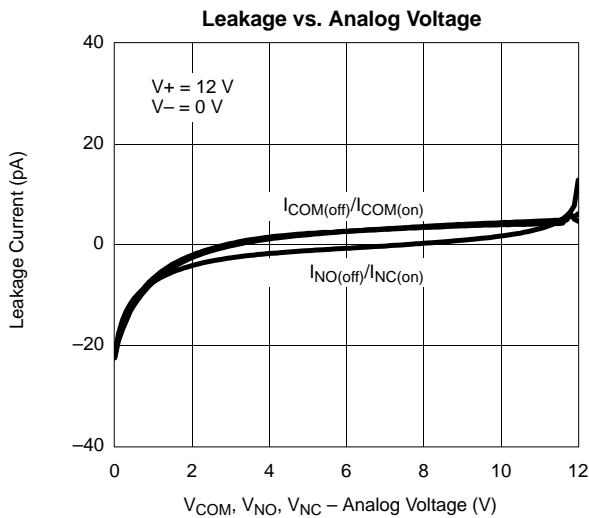


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)





TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



SCHEMATIC DIAGRAM (TYPICAL CHANNEL)

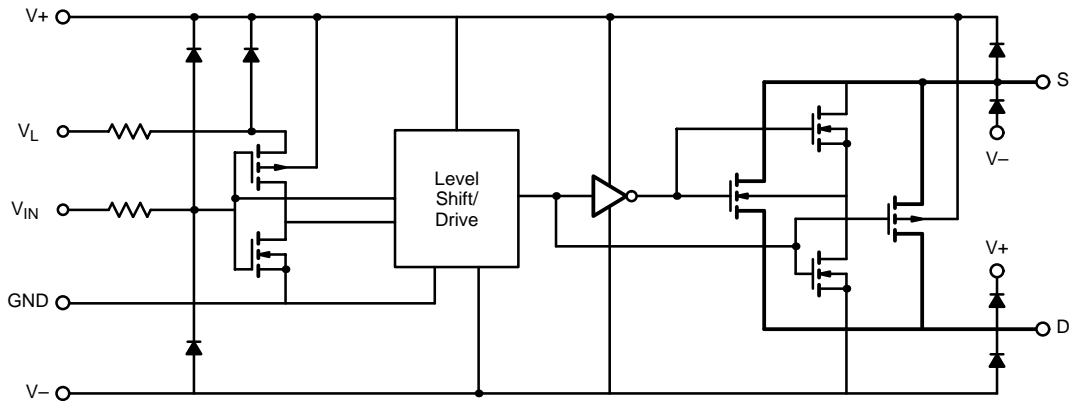
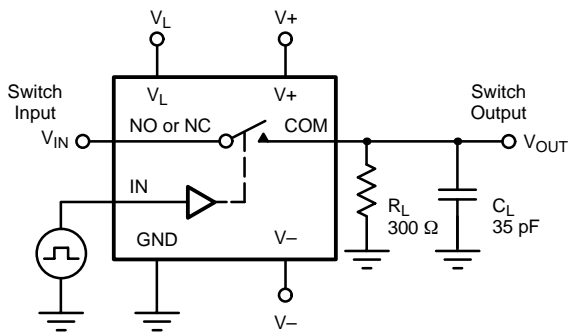


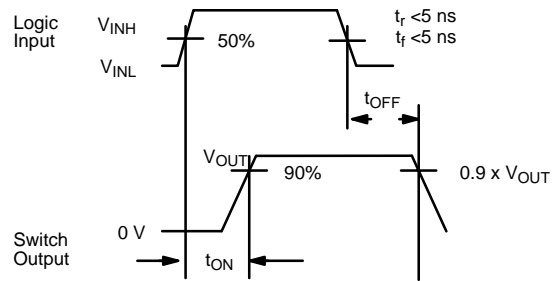
Figure 1.

TEST CIRCUITS



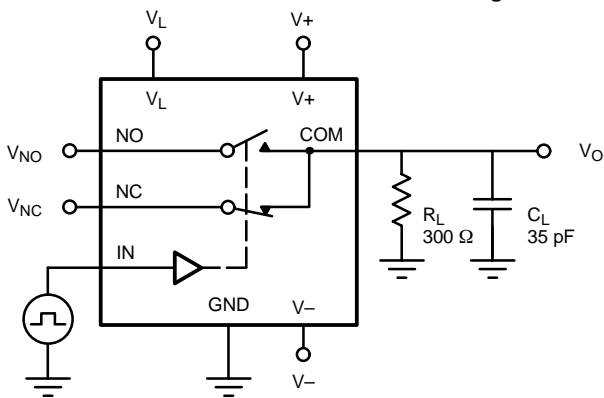
C_L (includes fixture and stray capacitance)

$$V_{OUT} = V_{IN} \frac{R_L}{R_L + r_{ON}}$$



Note: Logic input waveform is inverted for switches that have the opposite logic sense control

Figure 2. Switching Time



C_L (includes fixture and stray capacitance)

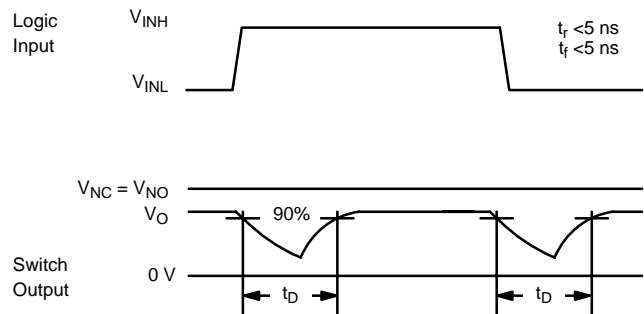
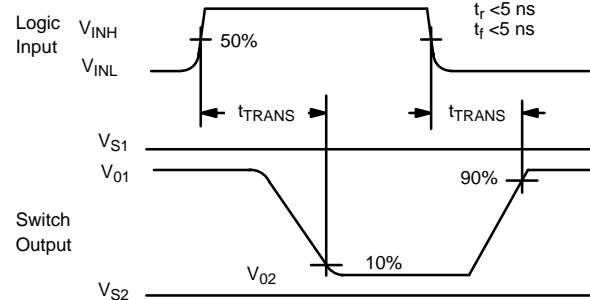
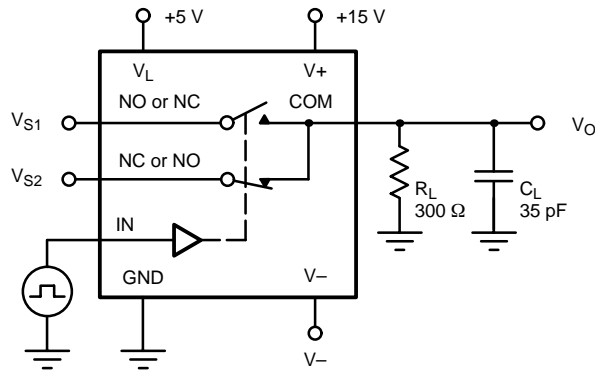


Figure 3. Break-Before-Make (DG419L)

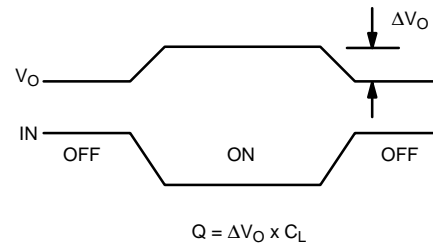
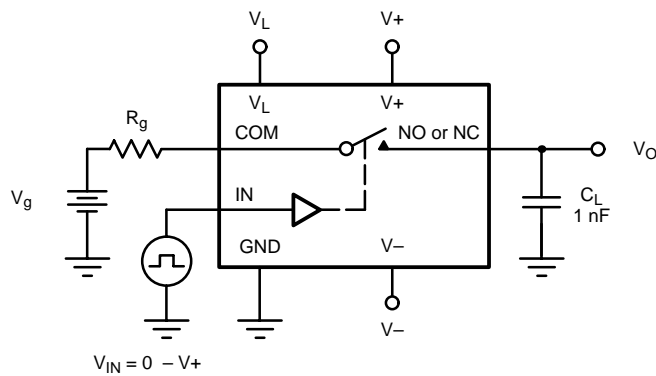
TEST CIRCUITS



C_L (includes fixture and stray capacitance)

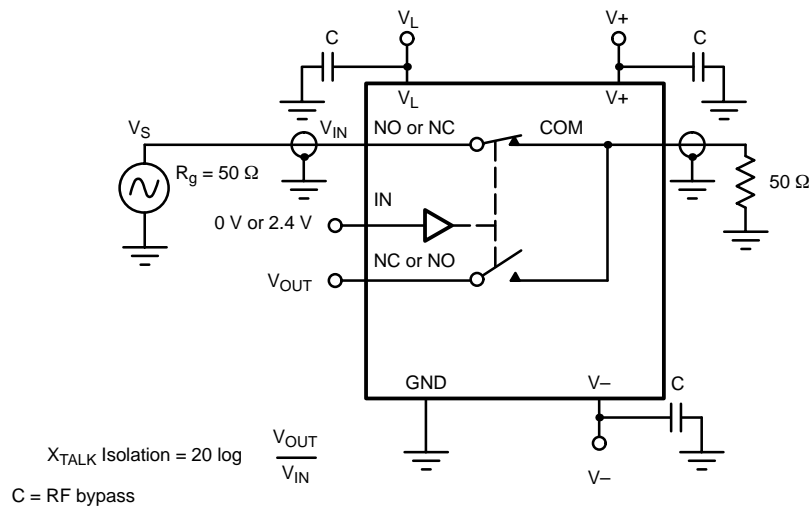
$$V_O = V_S \frac{R_L}{R_L + r_{ON}}$$

Figure 4. Transition Time (DG419L)



IN dependent on switch configuration Input polarity determined by sense of switch.

Figure 5. Charge Injection



$$X_{TALK} \text{ Isolation} = 20 \log \frac{V_{OUT}}{V_{IN}}$$

$C = \text{RF bypass}$

Figure 6. Crosstalk (DG419L)

TEST CIRCUITS

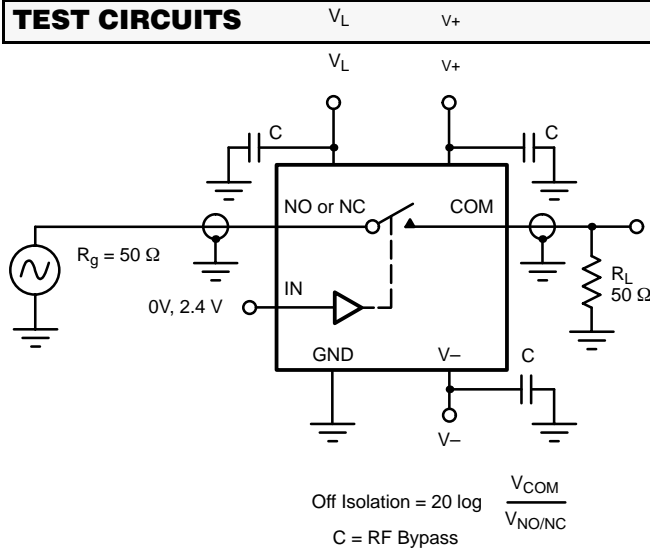


Figure 7. Off Isolation

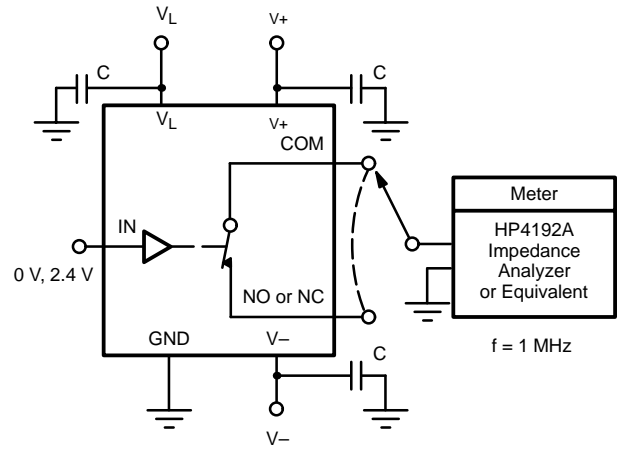


Figure 8. Source/Drain Capacitances